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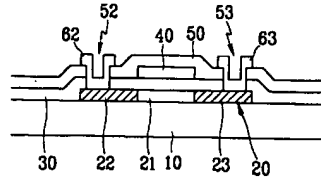
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(54) TFT

(57) Abstract:

PURPOSE: A TFT(Thin Film Transistor) is provided to obtain uniformly the mobility of the current of the TFT by forming a gate electrode having an arbitrary angle to the growing direction of a grain.

CONSTITUTION: A semiconductor layer(20) is formed with polysilicon. The semiconductor layer includes a channel region(21) and a source and a drain region(22,23) formed at both sides of the channel region. A gate insulating layer(30) is formed on the semiconductor layer. A gate electrode(40) is formed on an upper portion of the gate insulating layer of the channel region. The gate electrode has an arbitrary angle to the growing direction of a grain of the polysilicon. A source electrode(62) and a drain electrode(63) are connected to the source and the drain regions, respectively.



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Legal Status

Final disposal of an application (application)